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TRANSMITTAL FORM

(to be used for all correspondence after initial filing)

Total Number of Pages in This Submission	10

Patent Number	6,795,231 B1 10634179
Issue Date	September 21, 2004
First Named Inventor	Waclaw C. Koscielniak
Group Art Unit	2873
Examiner Name	Tuyen Q. Tra
Attorney Docket Number	100-15210 (P05000-D01)

ENCLOSURES *(check all that apply)*

- ☐ Fee Transmittal Form
  - ☐ Fee Attached
- ☐ Amendment/Response
  - ☐ After Final (Response)
  - ☐ Affidavits/declaration(s)
- ☐ Extension of Time Request
- ☐ Express Abandonment Request
- ☐ Information Disclosure Statement
- ☐ Certified Copy of Priority Document(s)
- ☐ Response to Missing Parts/ Incomplete Application
  - ☐ Response to Missing Parts under 37 CFR 1.52 or 1.53
- ☐ Assignment Papers *(for an Application)*
- ☐ Drawing(s)
- ☐ Licensing-related Papers
- ☐ Petition Routing Slip (PTO/SB/69) and Accompanying Petition
- ☐ Petition to Convert to a Provisional Application
- ☐ Power of Attorney, Revocation Change of Correspondence Address
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  Form PTO-1050 (in duplicate)

Remarks

Certificate
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of Correction

SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT

Firm or Individual name	Mark C. Pickering, Reg. No. 36,239
Signature	Mark C. Pickering
Date	September 28, 2004

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Certificate of Corrections Branch, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on this date: September 28, 2004

Typed or printed name	Robin L. King		
Signature	Robin L. King	Date	September 28, 2004

PATENT

Attorney Docket No. 100-15210 [P05000-D01]

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent of	Group Art Unit: 2873
Waclaw C. Koscielniak	Examiner: Tuyen Q. Tra
U.S. Pat. No. 6,795,231 B1	REQUEST FOR CERTIFICATE OF CORRECTION OF PATENT FOR PTO MISTAKES § 37 CFR 1.322(a)
Issued: September 21, 2004	
For: PHOTONIC CRYSTALS USING A SEMICONDUCTOR-BASED FABRICATION PROCESS (as amended)	

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450
Attention: Certificate of Corrections Branch

Sir:

Attached in duplicate is Form PTO-1050 with at least one copy being suitable for printing.

The exact column and line number where the errors occur in the Patent is:

This Certificate is necessitated through fault of the U.S. Patent and Trademark Office and no fee is required.

On the Cover Page,

At (57) after "the Abstract" delete "6 Claims" and insert --22 Claims--.

Claims 7-22 should be printed as follows:

--7. A photonic crystal formed on a semiconductor material of a first conductivity type, the semiconductor material having a top surface, the photonic crystal comprising:

a diffusion region of a second conductivity type formed in the semiconductor material; and

a plurality of spaced-apart stacks formed on the semiconductor material over the diffusion region, each stack having a plurality of layers of material and extending away from the top surface of the semiconductor material.

8. The crystal of claim 7 wherein the plurality of layers of material alternate between a first layer of material and a second layer of material, the first layer of material having a first dielectric constant, the second layer of material having a second dielectric constant.

9. The crystal of claim 8 and further comprising an interstack material formed over the semiconductor material between and adjoining the plurality of stacks.

10. The crystal of claim 9 wherein the interstack material has a top surface that is substantially coplanar with a top surface of each stack.

11. The crystal of claim 9 wherein the interstack material has a top surface that lies below a top surface of each stack.

12. The crystal of claim 9 wherein the interstack material has a top surface that lies above a top surface of each stack.

13. The crystal of claim 7 and further comprising an interstack material formed over the semiconductor material between and adjoining the plurality of stacks, the interstack material having a top surface that is substantially coplanar with a top surface of each stack.

14. The crystal of claim 7 and further comprising an interstack material formed over the semiconductor material between and adjoining the plurality of stacks, the interstack material having a top surface that lies below a top surface of each stack.

15. The crystal of claim 7 and further comprising an interstack material formed over the semiconductor material between and adjoining the plurality of stacks, the interstack material having a top surface that lies above a top surface of each stack.

16. A photonic crystal formed on a semiconductor material of a conductivity type, the semiconductor material having a top surface, the photonic crystal comprising:

an array of spaced-apart stacks formed on the semiconductor material, each stack having a plurality of layers of material and extending away from the top surface of the semiconductor material, the plurality of layers of material alternating between a first layer of material and a second layer of material, the first layer of material having a first dielectric constant, the second layer of material having a second dielectric constant; and

an interstack material formed over the semiconductor material between and

adjoining the plurality of stacks.

17. The crystal of claim 16 wherein the interstack material has a top surface that is substantially coplanar with a top surface of each stack.

18. The crystal of claim 16 wherein the interstack material has a top surface that lies below a top surface of each stack.

19. The crystal of claim 16 wherein the interstack material has a top surface that lies above a top surface of each stack.

20. The crystal of claim 16 wherein the interstack material has a top surface that is substantially coplanar with a top surface of each stack.

21. The crystal of claim 16 wherein the interstack material has a top surface that lies below a top surface of each stack.

22. The crystal of claim 16 wherein the interstack material has a top surface that lies above a top surface of each stack.--

Please send the Certificate to:

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Petaluma, CA 94953-0300
Customer No. 33402

Respectfully submitted,

Dated: 9-28-04

By: Mark C. Pickering

Mark C. Pickering
Reg. No. 36,239

Attorney for Assignee

OCT 0 8 2004

(Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO: 6,795,231 B1

DATED: September 21, 2004

INVENTOR(S): Koscielniak

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the Cover Page,

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8. The crystal of claim 7 wherein the plurality of layers of material alternate between a first layer of material and a second layer of material, the first layer of material having a first dielectric constant, the second layer of material having a second dielectric constant.

9. The crystal of claim 8 and further comprising an interstack material formed over the semiconductor material between and adjoining the plurality of stacks.

10. The crystal of claim 9 wherein the interstack material has a top surface that is substantially coplanar with a top surface of each stack.

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an interstack material formed over the semiconductor material between and adjoining the plurality of stacks.

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